

2SK213, 2SK214, 2SK215, 2SK216

Silicon N Channel MOS FET

REJ03G0903-0200

(Previous: ADE-208-1241)

Rev.2.00 Sep 07, 2005

Application

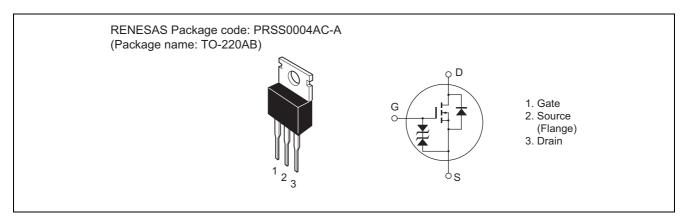
High frequency and low frequency power amplifier, high speed switching.

Complementary pair with 2SJ76, J77, J78, J79

Features

- Suitable for direct mounting
- High forward transfer admittance
- Excellent frequency response
- Enhancement-mode

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item		Symbol	Ratings	Unit
Orain to source voltage 2SK213		V_{DSX}	140	V
	2SK214		160	
	2SK215		180	
	2SK216		200	
Gate to source voltage		V_{GSS}	±15	V
Drain current		I _D	500	mA
Body to drain diode reverse drain current		I _{DR}	500	mA
Channel dissipation		Pch	1.75	W
		Pch*1	30	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-45 to +150	°C

Note: 1. Value at $T_C = 25^{\circ}C$

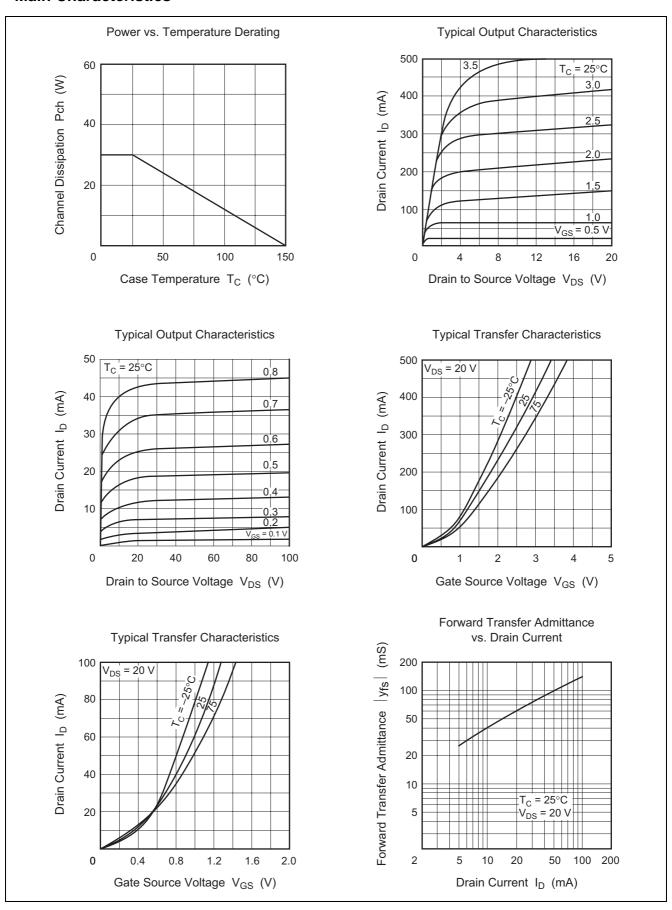
Electrical Characteristics

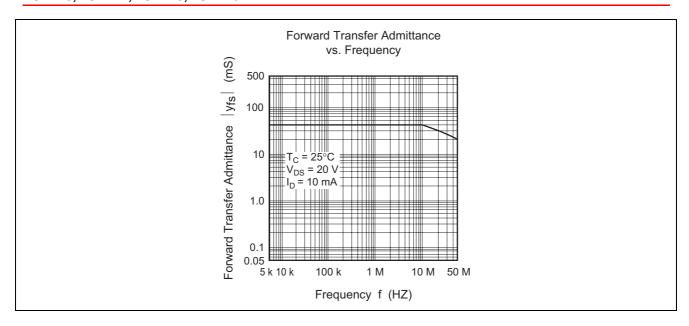
 $(Ta = 25^{\circ}C)$

Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown	2SK213	$V_{(BR)DSX}$	140	_	_	V	$I_D = 1 \text{ mA}, V_{GS} = -2 \text{ V}$
voltage	2SK214		160	_	_	V	
	2SK215		180	_	_	V	
	2SK216		200	_	_	V	
Gate to source breakdown voltage		$V_{(BR)GSS}$	±15	_	_	V	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0$
Gate to source voltage		V _{GS(on)}	0.2	_	1.5	V	$I_D = 10 \text{ mA}, V_{DS} = 10 \text{ V}^{*2}$
Drain to source saturation voltage		V _{DS(sat)}	_	_	2.0	V	$I_D = 10 \text{ mA}, V_{GD} = 0 *^2$
Forward transfer admittance		y _{fs}	20	40	_	mS	$I_D = 10 \text{ mA}, V_{DS} = 20 \text{ V}^{*2}$
Input capacitance		Ciss	_	90	_	pF	$I_D = 10 \text{ mA}, V_{DS} = 10 \text{ V},$
Reverse transfer capacitance		Crss	_	2.2	_	pF	f = 1 MHz

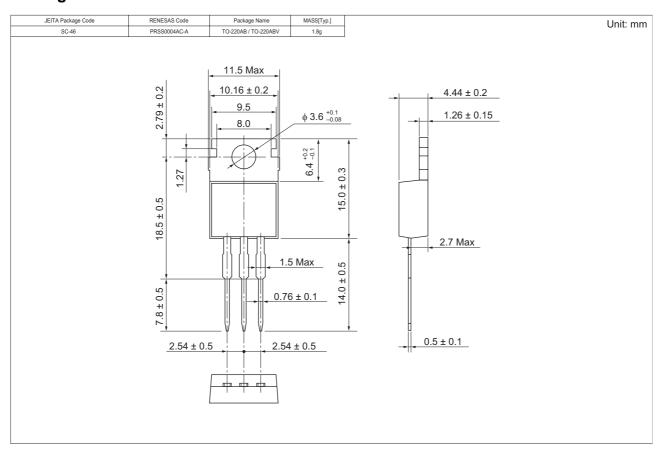
Note: 2. Pulse test

Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK213-E	500 pcs	Box (Sack)
2SK214-E	500 pcs	Box (Sack)
2SK215-E	500 pcs	Box (Sack)
2SK216-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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